

ABSTRACT

The present invention provides an etching method enabling selective etching of a film containing Si and O and not containing N, a method for manufacturing a semiconductor device using the etching method, an etching device, a surface treatment gas composition, and a surface treatment material-containing etching gas composition. The present invention relates to an etching method, including bringing (I) an etching gas composition containing HF gas and (II) a surface treatment gas composition containing a surface treatment material into contact with a substrate having a film at least containing Si and O and not containing N and a film at least containing Si and N to selectively etch the film containing Si and O and not containing N.

FIG.1